Product Summary

$V_{(BR)DSS}$	$R_{DS(on)\ max}$	I_D $T_A = 25°C$
-30V	8mΩ @ V_{GS} = -10V	-17A
	10.2mΩ @ V_{GS} = -4.5V	-14.5A

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **"Green" Device (Note 1)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

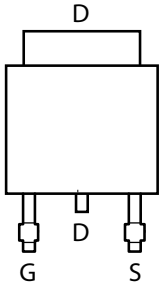
- DC-DC Converters
- Power management functions
- Backlighting

Mechanical Data

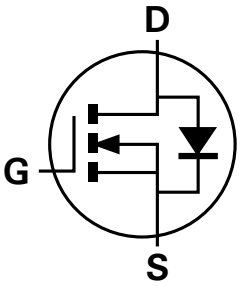
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

TO252

Top View



Top View
Pin-Out



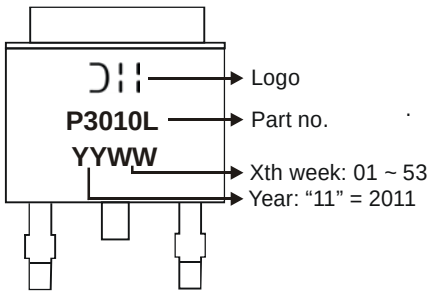
Equivalent Circuit

Ordering Information (Note 2)

Part Number	Qualification	Case	Packaging
DMP3010LK3-13	Commercial	TO252	2,500/Tape & Reel
DMP3010LK3Q-13	Automotive	TO252	2,500/Tape & Reel

Notes: 1. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
2. For packaging details, go to our website at http://www.diodes.com.

Marking Information



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 4) V_{GS} = -10V	Steady State	T_A = 25°C T_A = 70°C	I_D	-17.0 -13.0	A
	t<10s	T_A = 25°C T_A = 70°C	I_D	-27.0 -21.0	A
Continuous Drain Current (Note 4) V_{GS} = -4.5V	Steady State	T_A = 25°C T_A = 70°C	I_D	-14.5 -11.5	A
	t<10s	T_A = 25°C T_A = 70°C	I_D	-23.0 -18.0	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	-100	A
Maximum Body Diode Forward Current (Note 4)			I_S	5.5	A
Avalanche Current (Note 5)			I_{AS}	47	A
Avalanche Energy (Note 5)			E_{AS}	113	mJ

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 3)		P_D	1.7	W
Thermal Resistance, Junction to Ambient (Note 3)	Steady state	$R_{\theta JA}$	72	°C/W
	t<10s		29	°C/W
Total Power Dissipation (Note 4)		P_D	3.4	W
Thermal Resistance, Junction to Ambient (Note 4)	Steady state	$R_{\theta JA}$	37	°C/W
	t<10s		15	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.1	-1.6	-2.1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	6.5	8	mΩ	V_{GS} = -10V, I_D = -10A
		—	7.2	10.2		V_{GS} = -4.5V, I_D = -10A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	30	—	S	V_{DS} = -15V, I_D = -10A
Diode Forward Voltage	V_{SD}	—	-0.65	-1.0	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	6234	—	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	1500	—		
Reverse Transfer Capacitance	C_{rss}	—	774	—		
Gate Resistance	R_G	—	1.28	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	59.2	—	nC	V_{DS} = -15V, V_{GS} = -4.5V, I_D = -10A
Gate-Source Charge	Q_{gs}	—	16.1	—		
Gate-Drain Charge	Q_{gd}	—	15.7	—		
Turn-On Delay Time	$t_{D(on)}$	—	11.4	—	ns	V_{DS} = -15V, V_{GEN} = -10V, R_G = 6Ω, I_D = -1A
Turn-On Rise Time	t_r	—	9.4	—		
Turn-Off Delay Time	$t_{D(off)}$	—	260.7	—		
Turn-Off Fall Time	t_f	—	99.3	—		

Notes:
3. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
4. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
5 .UIS in production with L = 0.1mH, T_J = 25°C
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.

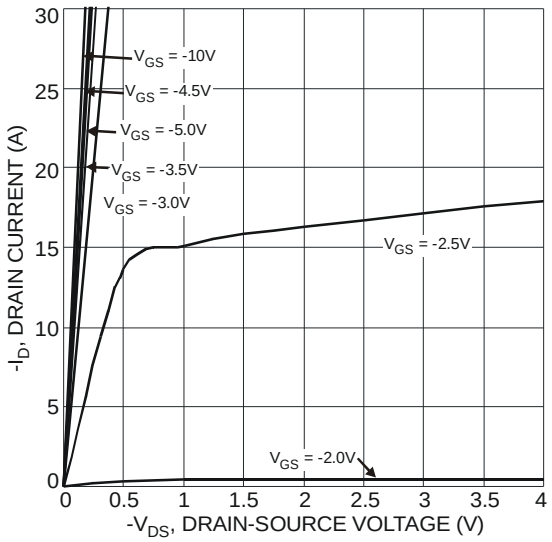


Fig. 1 Typical Output Characteristic

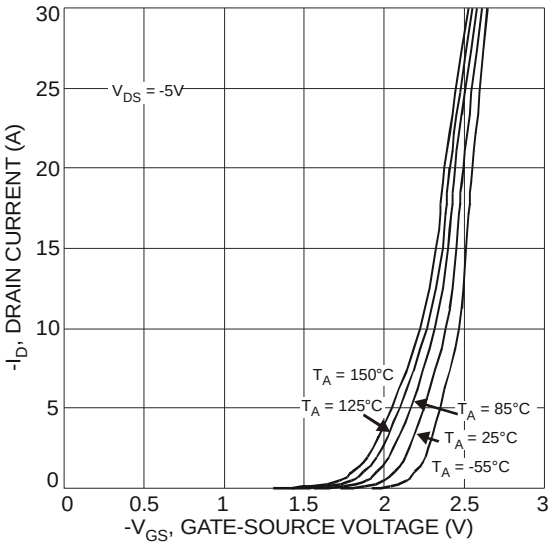


Fig. 2 Typical Transfer Characteristic

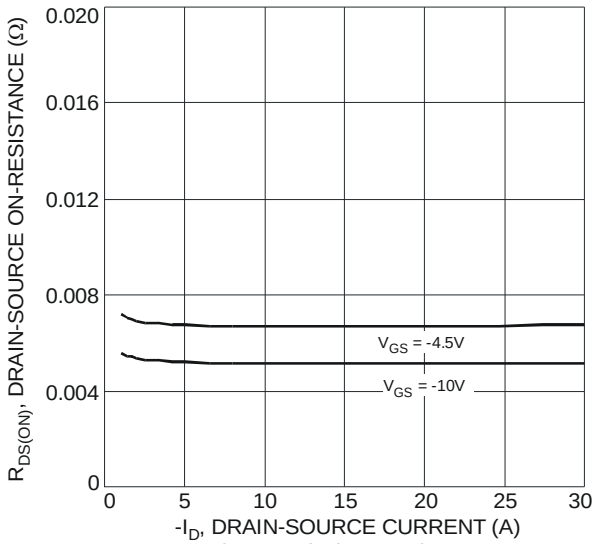


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

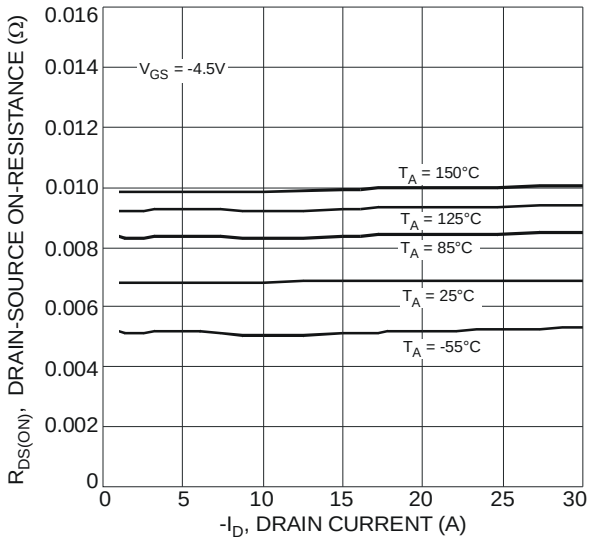


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

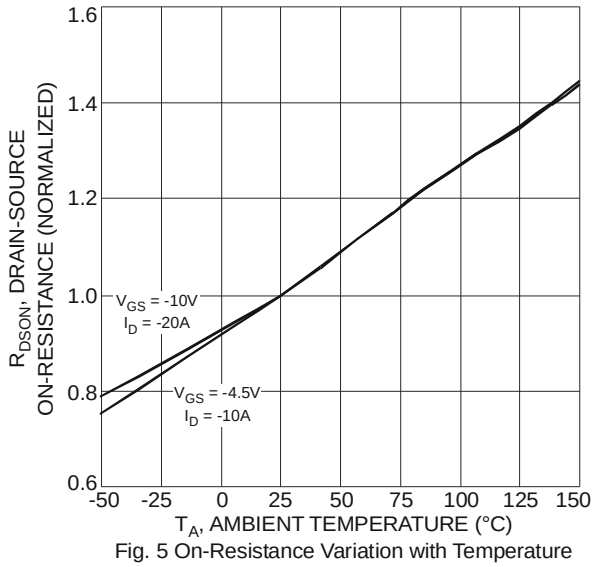


Fig. 5 On-Resistance Variation with Temperature

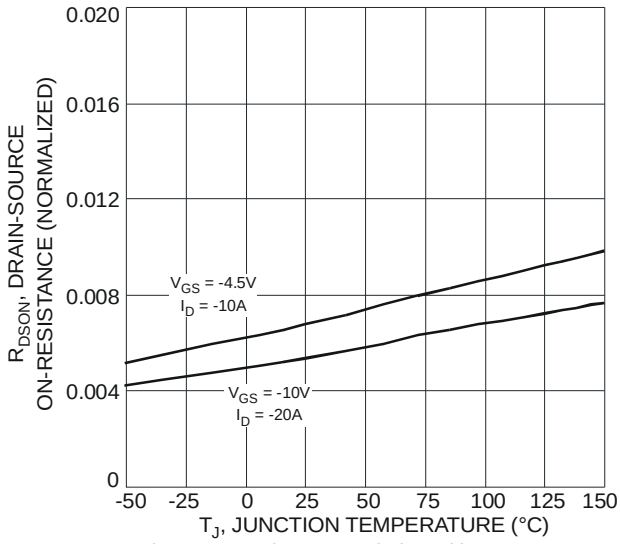


Fig. 6 On-Resistance Variation with Temperature

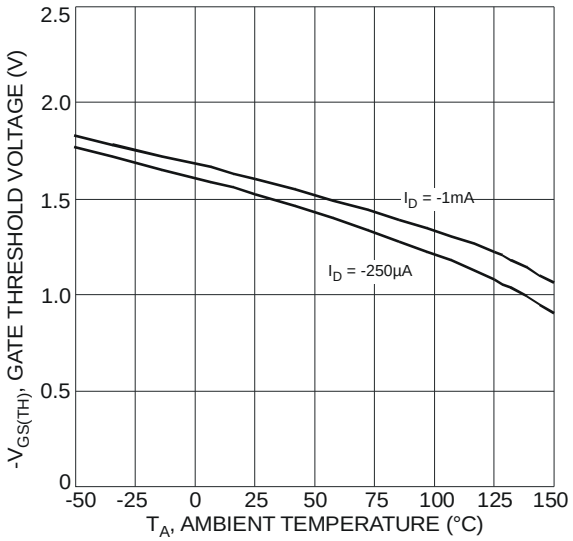


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

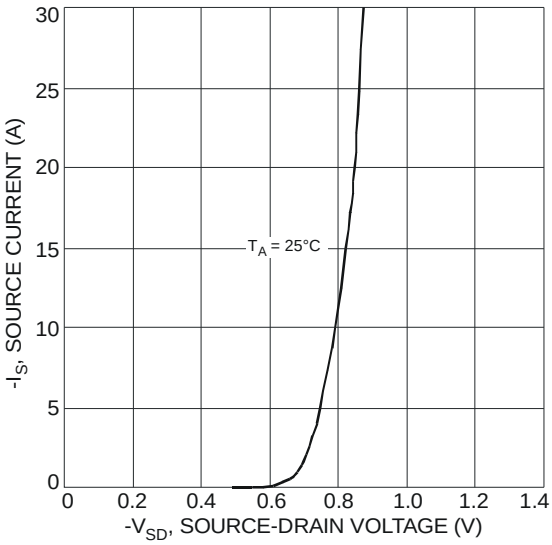


Fig. 8 Diode Forward Voltage vs. Current

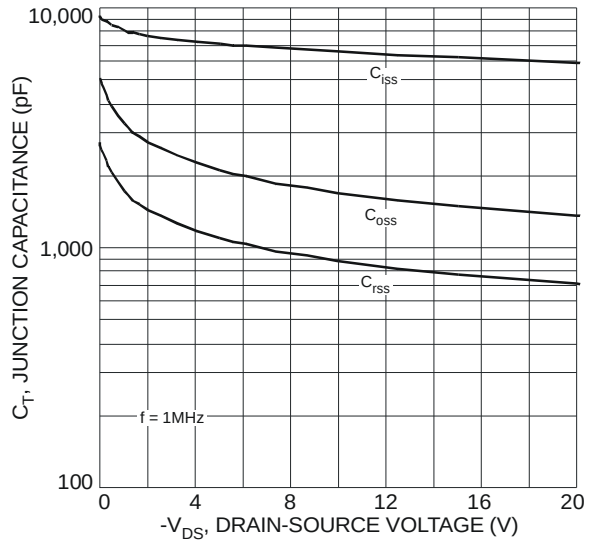


Fig. 9 Typical Total Capacitance

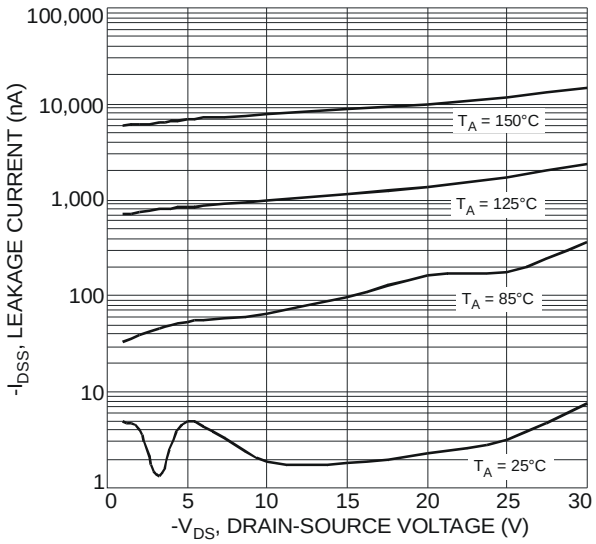


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

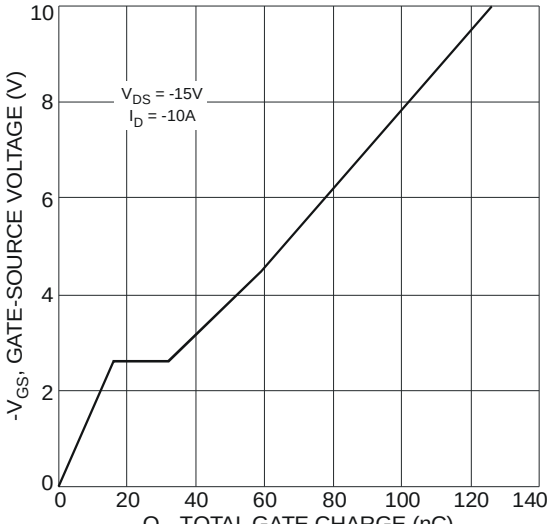


Fig. 11 Gate-Source Voltage vs. Total Gate Charge

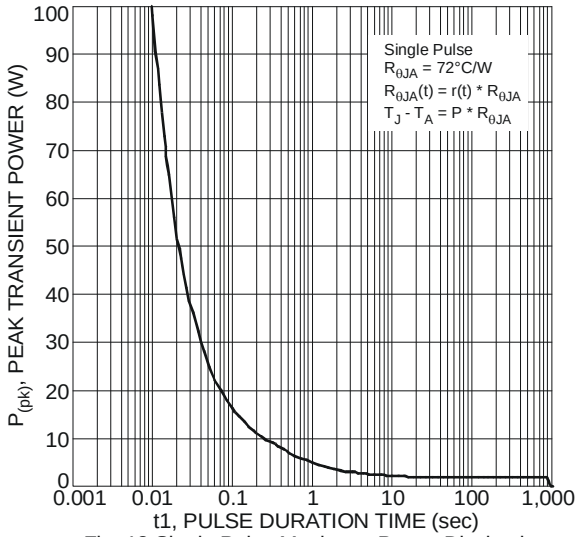


Fig. 12 Single Pulse Maximum Power Dissipation

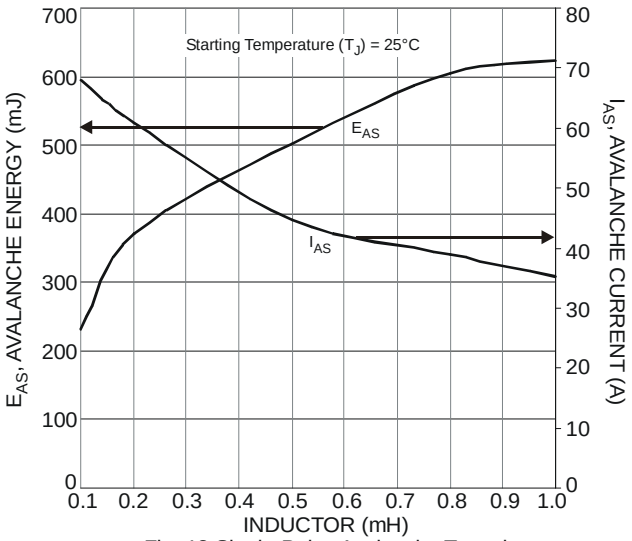


Fig. 13 Single-Pulse Avalanche Tested

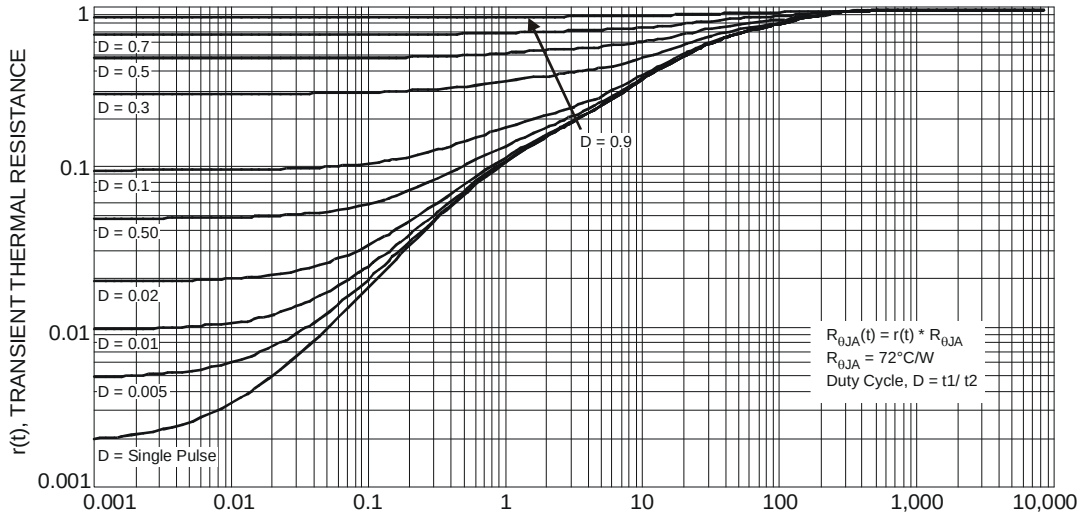
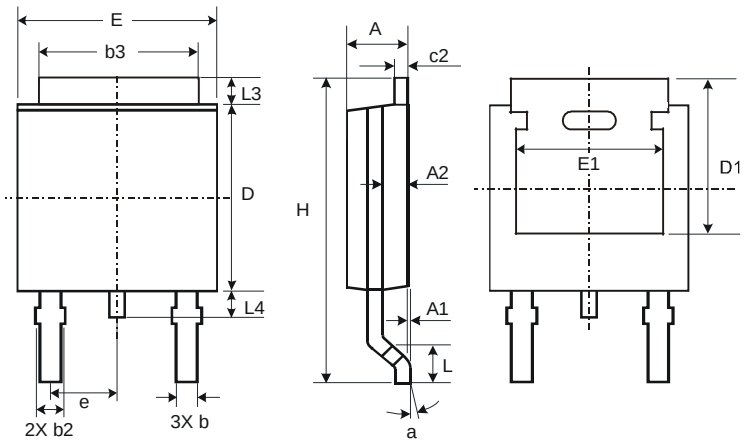


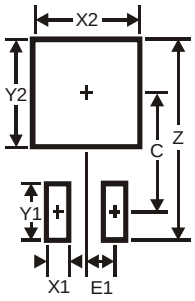
Fig. 14 Transient Thermal Resistance

Package Outline Dimensions



TO252			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	–	–
e	–	–	2.286
E	6.45	6.70	6.58
E1	4.32	–	–
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	–
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

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